

INFORMA TOMOLUNG DISCLOSURE **CITATION**

Customer Number 26615

APPLICATION NO. ATTORNEY'S DKT NO. 10/653,105 H1492 APPLICANT(S) Bin Yu et al. FILING DATE GROUP September 3, 2003 -2829-

PTO-1449		Sep		September 3,	September 3, 2003		-2829 - ZBII		
U.S. PATENT DOCUMENTS									
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME		CLASS	SUBCLASS	FILING DATE		
V	US 2002/0125536 A1	09-12-02	Iwasa et al.		257	368	07-18-01		
Vu	US 2002/0153587 A1	10-24-02	Adkisson et al.		257	510	07-02-02		
علا	US 2002/0177263 A1	11-28-02	Hanafi et al.		438	183	05-24-01		
Vu	6,359,311 B1	03-19-02	Colinge et al.		257	347	01-17-01		
FOREIGN PATENT DOCUMENTS									
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY		CLASS	SUBCLASS	Trans	No No	
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Jong-Tae Park et al.: "Multiple-Gate SOI MOSFETs: Device Design Guidelines," IEEE Transactions on Electron Devices, Vol. 49, No. 12, December 2002, pp. 2222-2229. Fu-Liang Yang et al.: "25 nm CMOS Omega FETs," International Electron Devices Meeting 2002, IEDM, Technical Digest, December 8-11, 2002 in New York, NY, pp. 255-258. Toshikazu Mukaiyama et al.: "Fabrication of Gate-All-Around MOSFET By Silicon Anisotropic Etching Technique," Solid State Electronics, Elsevier Science Publishers, Vol. 42, No. 7-8, July 8, 1998, pp. 1623-1626. Yang-Kyu Choi et al.: "Spacer FinFET: nanoscale double-gate CMOS technology for the terabit era," Solid State Electronics, Elsevier Science Publishers, Vol. 46, No. 10, October 2002, pp. 1595-1601. Effendi Leobandung et al.: "Wire-channel and wrap-around-gate metal-oxide-semiconductor field-effect transistors with a significant reduction of short channel effects," 41st International Conference on Electron, Ion, and Photon Beams Technology and Nanofabrication in Dana Point, CA, May 27-30, 1997, Vol. 15, No. 6, Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures), November-December 1997, AIP for American Vacuum Soc., pp. 2791-2794. PCT International Search Report mailed July 13, 2004, 5 pages.									
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